

FORM PTO-1449

U.S. Department of Commerce
Patent and Trademark OfficeAttorney Docket Number
5308-157IP2Serial No.
10/045,542

LIST OF DOCUMENTS CITED BY APPLICANT

(Use several sheets if necessary)

Applicants: Das et al.

Filing Date: October 26, 2001

Group: 1762

U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
7	1	3,924,024	12/2/75	Naber et al.	427	95	
	2	4,466,172	8/21/84	Batra	29	571	
	3	4,875,083	10/17/89	Palmour	357	23.6	
	4	5,170,455	12/8/92	Goossen et al.	385	89	
	5	5,184,199	2/2/93	Fujii et al.	29	10	
	6	5,506,421	4/9/96	Palmour	257	77	
	7	5,510,630	4/23/96	Agarwal et al.	257	77	
	8	5,726,463	3/10/98	Brown et al.	257	77	
	9	5,763,905	6/9/98	Harris	257	77	
	10	5,837,572	11/17/98	Gardner et al.	438	199	
	11	5,939,763	8/17/99	Hao et al.	257	411	
	12	5,960,289	9/28/99	Tsui et al.	438	257	
	13	5,972,801	10/26/99	Lipkin et al.	438	770	
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17	21	6,344,663 B1	2/5/02	Slater, Jr. et al.	257	77	

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7	23	0 637 069 B1	1/31/01	EPO	—	—	
7	24	WO 97/17730	5/15/97	PCT	—	—	

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7	25	WO 97/39485	10/23/97	PCT			
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✓	7	26	M. K. Das, L.A. Lipkin, J.W. Palmour, G.Y. Chung, J.R. Williams, K. McDonald, and L.C. Feldman, "High Mobility 4H-SiC Inversion Mode MOSFETs Using Thermally Grown, NO Annealed SiO ₂ ," <i>IEEE Device Research Conference</i> , Denver, CO June 19-21, 2000.				
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